TIGER ELECTRONIC CO.,LTD

Product specification

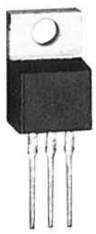
Complementary Silicon Power Ttransistors — 2SB546A / 2SD401A

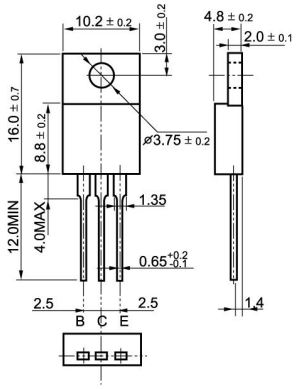
(Ta = 25 °C)

DESCRIPTION

The 2SB546A and 2SD401A are high voltage triple diffused silicon transistors,
These devices are designed for use in line-operated color TV vertical defiection of complementary symmetry circuit,
The 2SB546A and 2SD401A are complementary transistors, consisting of straight leads

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2.0	A
Collector Peak Current	$I_{C(peak)}$	3.0	A
Total Dissipation at	P_{tot}	30	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C





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ELECTRICAL CHARACTERISTICST SEMICONDUCTOR CO., LTD

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=150V, I_E=0	—	—	50	uA
Emitter Cut-off Current	I_{EBO}	V_{EB}=4.0V, I_C=0	—	—	50	uA
Collector-Emitter Sustaining Voltage	V_{CEO}	I_C=10mA, I_B=0	150	—	—	V
DC Current Gain	$h_{FE(1)}$	V_{CE}=10V, I_C=400mA	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA,I_B=50mA	—	—	2.0	V
Collector capacitance	C_C	V_{CB}=10V,f=1.0MHz, I_E=0	—	75/45	—	pF
Transition Frequency	f_T	V_{CE}=10V,I_C=400mA	—	7.0	—	MHz